

Title (en)
SEMICONDUCTOR PACKAGE, SEMICONDUCTOR DEVICE, ELECTRONIC DEVICE, AND METHOD OF MANUFACTURING SEMICONDUCTOR PACKAGE

Title (de)
HALBLEITERGEHÄUSE, HALBLEITER, ELEKTRONIKELEMENT UND HERSTELLUNG EINES HALBLEITERGEHÄUSES

Title (fr)
BOITIER A SEMI-CONDUCTEUR, DISPOSITIF SEMI-CONDUCTEUR, DISPOSITIF ELECTRONIQUE ET PROCEDE DE FABRICATION DE BOITIER A SEMI-CONDUCTEUR

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EP 1107307 A8 20011121 (EN)

Application
EP 00935668 A 20000613

Priority
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Abstract (en)
[origin: EP1107307A1] An insulating layer (3) having an opening portion (3a) at a position conformable to an electrode pad (2) is formed. Next, a resin projection portion (4) is formed on the insulating layer (3). Thereafter, a resist film is formed which has opening portions made in regions conformable to the opening portion (3a), the resin projection portion (4) and the region sandwiched therebetween. A Cu plating layer (6) is formed by electrolytic copper plating, using the resist film as a mask. <IMAGE>

IPC 1-7
H01L 21/60; **H01L 23/12**

IPC 8 full level
H01L 21/56 (2006.01); **H01L 23/31** (2006.01); **H01L 23/485** (2006.01); **H01L 23/525** (2006.01)

CPC (source: EP US)
H01L 21/56 (2013.01 - EP US); **H01L 23/3107** (2013.01 - EP US); **H01L 23/3114** (2013.01 - EP US); **H01L 23/525** (2013.01 - EP US); **H01L 24/02** (2013.01 - EP); **H01L 24/03** (2013.01 - EP); **H01L 24/05** (2013.01 - EP); **H01L 24/10** (2013.01 - EP US); **H01L 24/13** (2013.01 - EP US); **H01L 2224/02125** (2013.01 - EP US); **H01L 2224/0231** (2013.01 - EP US); **H01L 2224/02351** (2013.01 - EP US); **H01L 2224/0236** (2013.01 - EP); **H01L 2224/02377** (2013.01 - EP); **H01L 2224/0401** (2013.01 - EP US); **H01L 2224/05124** (2013.01 - EP US); **H01L 2224/05147** (2013.01 - EP US); **H01L 2224/05155** (2013.01 - EP US); **H01L 2224/05166** (2013.01 - EP US); **H01L 2224/05171** (2013.01 - EP US); **H01L 2224/05548** (2013.01 - EP US); **H01L 2224/05567** (2013.01 - EP US); **H01L 2224/05572** (2013.01 - EP US); **H01L 2224/05644** (2013.01 - EP US); **H01L 2224/13** (2013.01 - EP US); **H01L 2224/13021** (2013.01 - EP US); **H01L 2224/13022** (2013.01 - EP US); **H01L 2224/13023** (2013.01 - EP US); **H01L 2224/13024** (2013.01 - EP); **H01L 2224/13099** (2013.01 - EP US); **H01L 2924/0001** (2013.01 - EP); **H01L 2924/0002** (2013.01 - EP US); **H01L 2924/01004** (2013.01 - EP US); **H01L 2924/01005** (2013.01 - EP US); **H01L 2924/01006** (2013.01 - EP US); **H01L 2924/01013** (2013.01 - EP US); **H01L 2924/01015** (2013.01 - EP US); **H01L 2924/01022** (2013.01 - EP US); **H01L 2924/01024** (2013.01 - EP US); **H01L 2924/01029** (2013.01 - EP US); **H01L 2924/01033** (2013.01 - EP US); **H01L 2924/01078** (2013.01 - EP US); **H01L 2924/01079** (2013.01 - EP US); **H01L 2924/014** (2013.01 - EP US); **H01L 2924/10329** (2013.01 - EP US); **H01L 2924/14** (2013.01 - EP US); **H01L 2924/15311** (2013.01 - EP US)

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